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RFMD Releases Family of Linear GaN Power Transistors

MUNICH, Germany, Nov. 13, 2012 (GLOBE NEWSWIRE) -- RF Micro Devices, Inc. (Nasdaq:RFMD), a global leader in the design and manufacture of high-performance radio frequency components and compound semiconductor technologies, today announced that RFMD has production released two highly linear gallium nitride (GaN) RF unmatched power transistors (UPTs)—RFHA3942 (35W) and RFHA3944 (65W)—that deliver superior linear performance versus competing GaN transistors.

The release of the RFHA3942 and RFHA3944 follows the previous release of the RF393X series of UPTs targeting continuous wave (CW) and pulsed peak power applications. This new series of linear GaN discrete amplifiers is optimized for broadband applications requiring linear back-off operation or reduced spurious performance. RFMD plans to further its technology leadership position with future releases of 10W and 95W linear GaN devices over the next 12 months, significantly expanding the GaN UPT options available to RFMD's customers.

RFMD's highly linear GaN UPTs target new and existing communication architectures requiring improved broadband linear performance in support of high peak-to-average modulation waveforms. The RFHA3942 and RFHA3944 are tunable over a broad frequency range (DC to 4GHz) and provide CW peak power of 35W and 65W respectively. They also offer high gain of 15dB and high peak efficiency of > 55%. Using an IS95 9.8dB PAR signal tuned to 2.1GHz, the RFHA3942 achieves -43dBc adjacent channel power (ACP) at 34dBm POUT and the RFHA3944 achieves -54dBc ACP at 37dBm POUT. Additionally, the RFHA3942 and RFHA3944 offer high terminal impedance at the input and output of the package, enabling wideband gain and power performance advantages in a single amplifier. The RFHA3942 and RFHA3944 are packaged in a flanged ceramic two-leaded package that leverages RFMD's advanced heat-sink and power-dissipation technologies to deliver excellent thermal stability and conductivity.

Jeff Shealy, vice president and general manager of RFMD's Power Broadband business unit, said, "RFMD is very pleased to expand its GaN-based product portfolio, offering industry-leading linear power performance in support of diverse end markets. RFMD's GaN product portfolio clearly demonstrates our continued commitment to technology and product leadership, and we look forward to introducing additional GaN devices that feature superior power density, high efficiency, rugged dependability, and 'green' power consumption advantages."

RFMD is showcasing a broad portfolio of industry-leading RF components at the Electronica 2012 trade show in Munich, Germany, November 13-16, Stand #A4.134. Samples and production quantities are available now through RFMD's online store or through local RFMD sales channels. Datasheets can be obtained via RFMD's website at www.rfmd.com or by contacting RFMD at 336-664-1233.

About RFMD

RF Micro Devices, Inc. (Nasdaq:RFMD) is a global leader in the design and manufacture of high-performance radio frequency components and compound semiconductor technologies. RFMD's products enable worldwide mobility, provide enhanced connectivity and support advanced functionality in the mobile device, wireless infrastructure, wireless local area network (WLAN or WiFi), cable television (CATV)/broadband, Smart Energy/advanced metering infrastructure (AMI), and aerospace and defense markets. RFMD is recognized for its diverse portfolio of semiconductor technologies and RF systems expertise and is a preferred supplier to the world's leading mobile device, customer premises and communications equipment providers.

Headquartered in Greensboro, N.C., RFMD is an ISO 9001-, ISO 14001-, and ISO/TS 16949-certified manufacturer with worldwide engineering, design, sales and service facilities. RFMD is traded on the NASDAQ Global Select Market under the symbol RFMD. For more information, please visit RFMD's web site at www.rfmd.com.

The RF Micro Devices, Inc. logo is available at http://www.globenewswire.com/newsroom/prs/?pkgid=6436

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update

any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements, other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and uncertainties, including variability in operating results, risks associated with the impact of global macroeconomic and credit conditions on our business and the business of our suppliers and customers, our reliance on a few large customers for a substantial portion of our revenue, the rate of growth and development of wireless markets, our ability to bring new products to market, our reliance on inclusion in third party reference designs for a portion of our revenue, our ability to manage channel partner and customer relationships, risks associated with the operation of our wafer fabrication, molecular beam epitaxy, assembly and test and tape and reel facilities, our ability to complete acquisitions and integrate acquired companies, including the risk that we may not realize expected synergies from our business combinations, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, raw material costs and availability, our ability to reduce costs and improve margins in response to declining average selling prices, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on gallium arsenide (GaAs) for the majority of our products, dependence on third parties, and substantial reliance on international sales and operations. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K and other reports and statements filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

CONTACT: At RFMD

Doug DeLieto

VP, Investor Relations

336-678-7088

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